

Total number of printed pages-5

53 (IE 502) TDEN

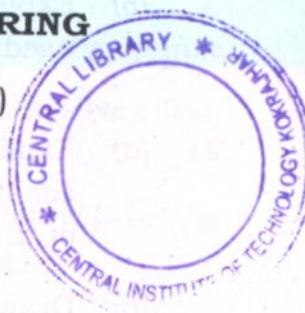
2019

TRANSDUCER ENGINEERING

Paper : IE 502 (Backlog)

Full Marks : 100

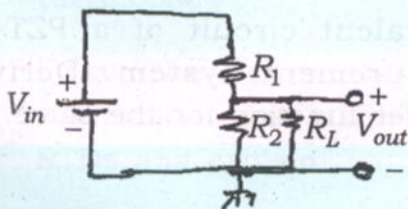
Time : Three hours



The figures in the margin indicate full marks for the questions.

Answer **any five** questions.

1. (a) For the following figure, derive the expression of the output voltage (V_{out}) when load resistance (i) $R_L \neq \infty$ and (ii) $R_L = \infty$.



Contd.

Determine the volume of V_{out} when
 $R_1 = 4.7k\Omega$, $R_2 = 3.3k\Omega$, $R_L = 0.5k\Omega$
and $V_{in} = 5Volts$. 12

(b) Explain, how a potentiometer can be used to measure liquid level. 8

2. (a) Explain, with a schematic diagram, the construction and the working principle of an LVDT. 10

(b) Draw the input-output characteristics of an LVDT and explain. What is residual voltage and how it can be eliminated? 10

3. (a) Define: charge sensitivity, voltage sensitivity and pressure sensitivity of a Piezoelectric transducer. Derive the different relations between them. 8

(b) Draw the block diagram and electrical equivalent circuit of a PZT-based measurement system. Derive the transfer function for the same. 12

4. (a) Define the gauge factor of strain gauge. Prove that $G_f = 1 + 2\nu + \frac{\Delta\rho/\rho}{\Delta l/l}$, where

G_f is the gauge factor, ν is the Poisson's ratio and $\frac{\Delta\rho/\rho}{\Delta l/l}$ is the change in resistance due to Piezoresistive effect. 10

(b) Explain the operation of full-bridge strain measurement system. 6

(c) A strain gauge of 120Ω nominal resistance is fixed on a steel frame subjected to a strain of $250\mu m/m$. If the gauge factor is 2.0, determine the change in gauge resistance. 4

5. (a) Explain the Law of intermediate temperature and the Law of intermediate metal. What is thermopile? 8

(b) Draw the schematic diagram for connection of a 3-Wire and a 4-Wire RTDs and explain. 8



(c) For a certain thermistor, $\beta = 3200K$ and its resistance at $20^\circ C$ is known to be 1056Ω . The thermistor is used for temperature measurement and the measured resistance is 2325Ω . Find the measured temperature. What will be the thermistor's new resistance if the temperature is increased to $55^\circ C$?

4

6. (a) Explain, with schematic diagram, the working principle of an Eddy-current sensor.

10

(b) A Hall effect element used for measuring a magnetic field strength gives an output voltage of $12.3mV$. The element is made of Silicon and is $5mm$ thick and carries a current of $2A$. The Hall coefficient for Silicon is $3.8 \times 10^{-6} Vm/A - Wb/m^2$. Determine the magnetic field strength.

6

(c) Mention four applications of Smart Sensors.

4

7. Write short notes on **any four** of the following:
 $4 \times 5 = 20$

- (a) Semiconductor-based temperature measurement technique
- (b) Capacitive type accelerometer
- (c) Cold-junction Compensation technique for T/c .
- (d) Villari effect and its applications
- (e) Angular displacement measurement using potentiometer
- (f) Photoresistive transducer and its applications.

